FIG. 1A

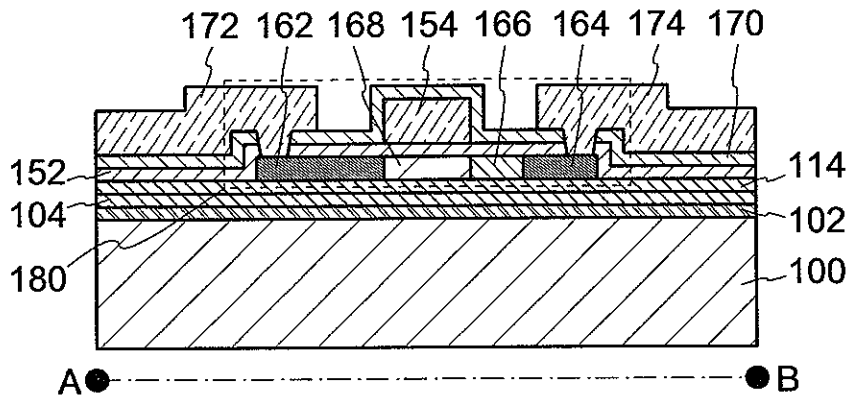

172
162
168
154
166
164
174
170
152
114
104
102
180
100
A
B

FIG. 1B

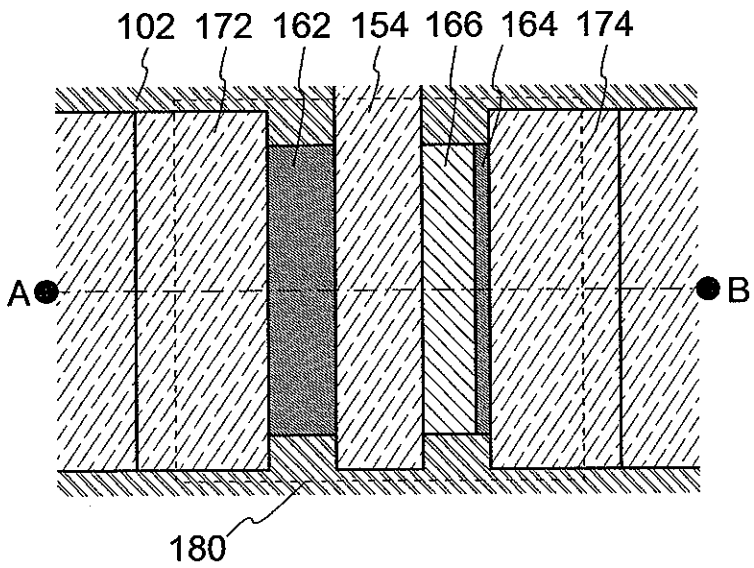

102
172
162
154
166
164
174
A
B
180

FIG. 2A

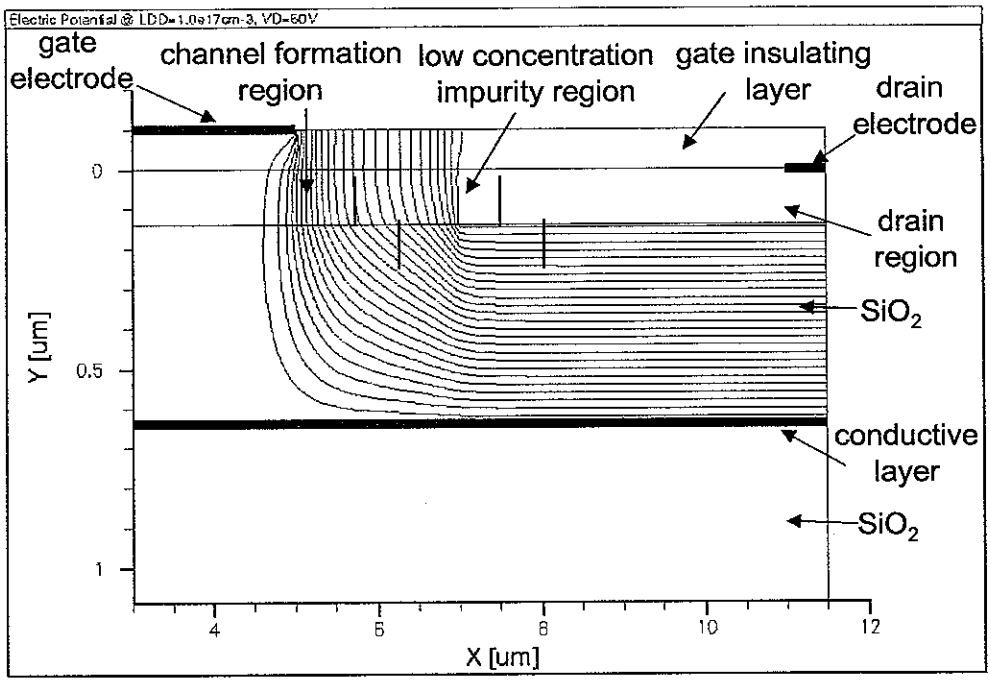

Electric Potential @ LDD=1.0e17cm-3, VD=60V
gate electrode
channel formation region
low concentration impurity region
gate insulating layer
drain electrode
drain region
SiO2
conductive layer
SiO2
Y [um]
X [um]
0
0.5
1
4
6
8
10
12

FIG. 2B

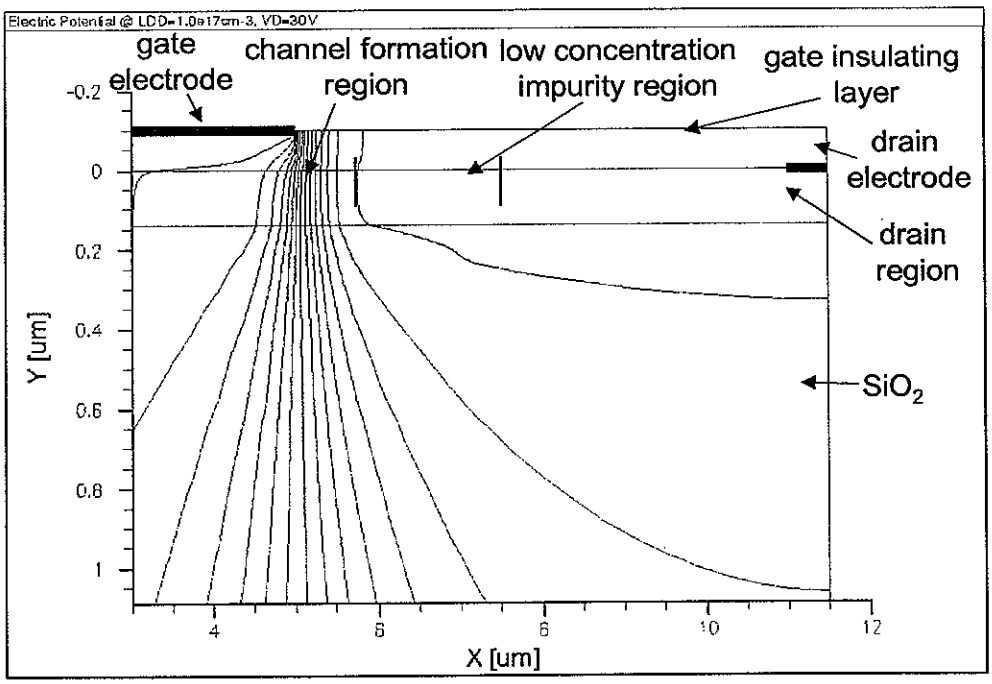

Electric Potential @ LDD=1.0e17cm-3, VD=30V
gate electrode
channel formation region
low concentration impurity region
gate insulating layer
drain electrode
drain region
SiO2
Y [um]
X [um]
-0.2
0
0.2
0.4
0.6
0.8
1
4
6
8
10
12

FIG. 3A

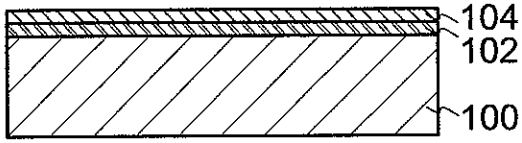


FIG. 3B

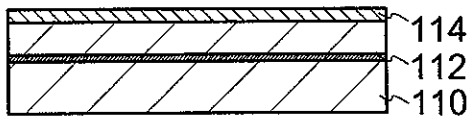


FIG. 3C

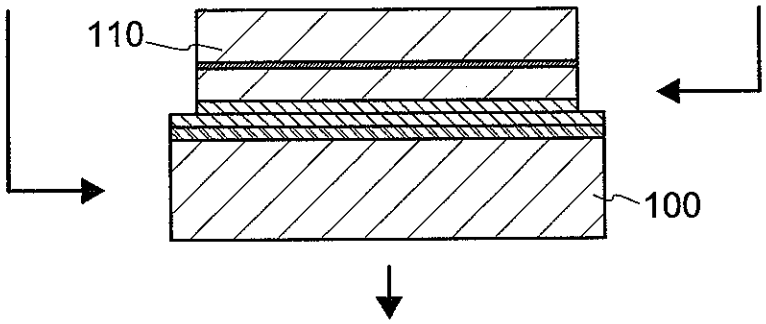


FIG. 3D

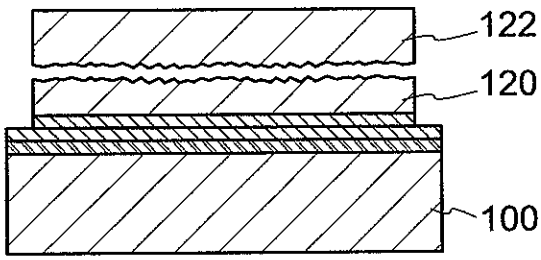


FIG. 3E

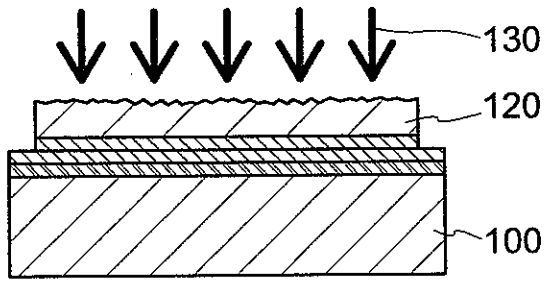


FIG. 3F

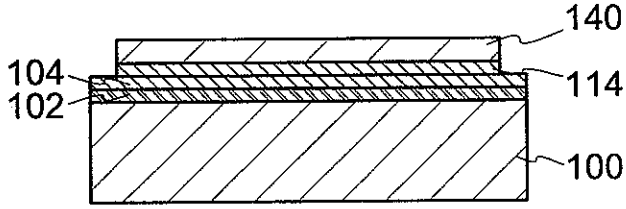


FIG. 4A

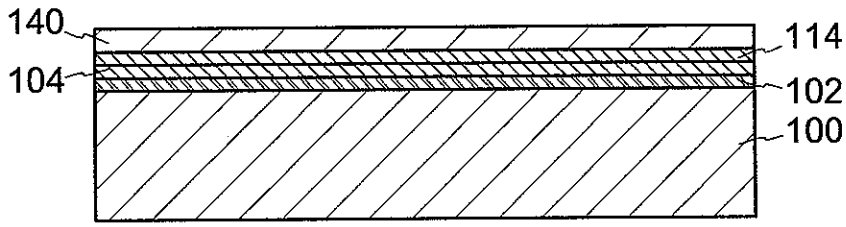


FIG. 4B

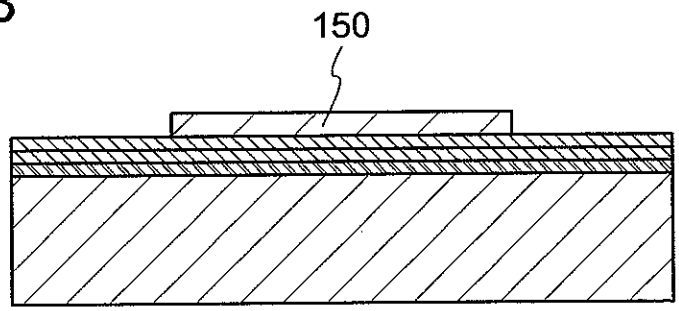


FIG. 4C

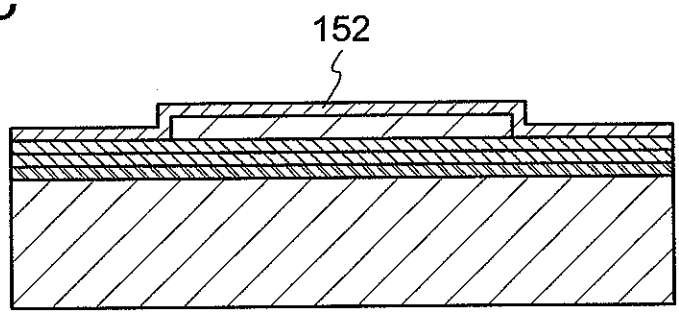


FIG. 4D

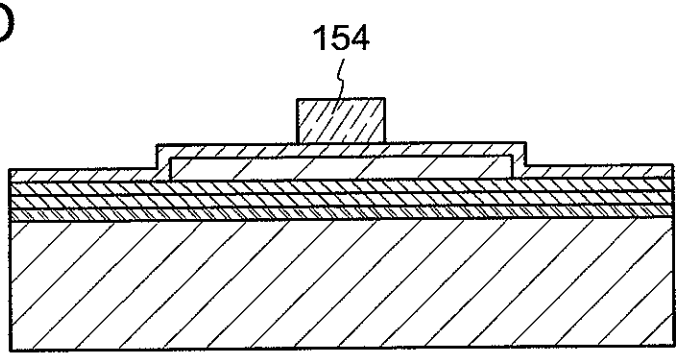


FIG. 5A

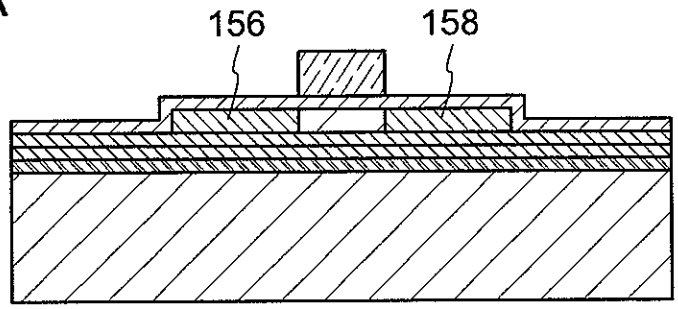


FIG. 5B

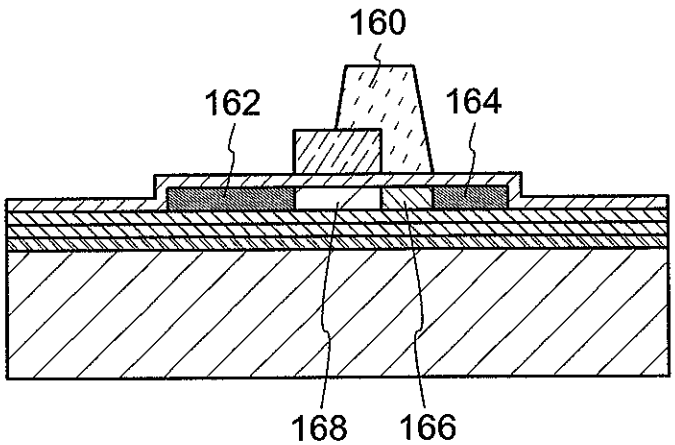


FIG. 5C

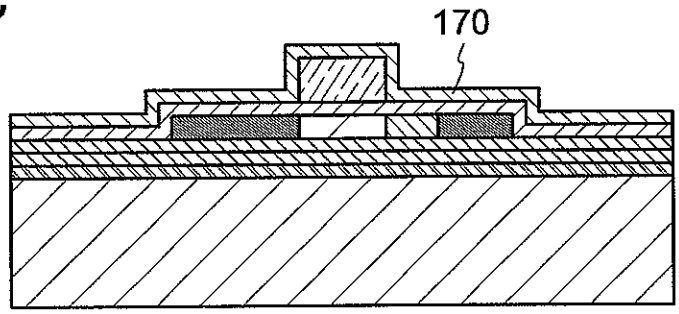


FIG. 5D

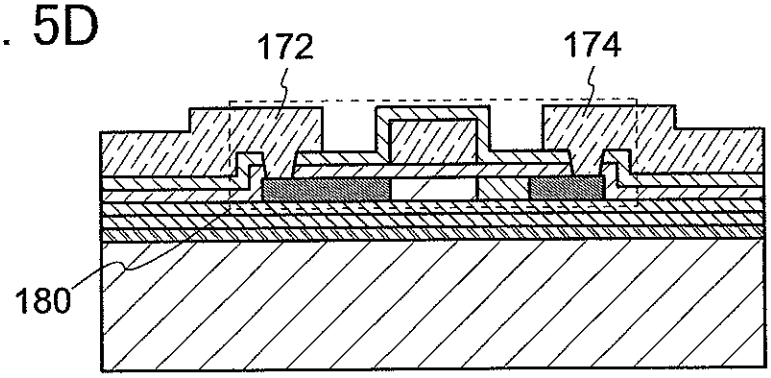


FIG. 6A

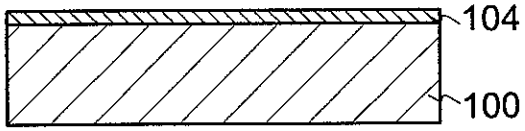


FIG. 6B

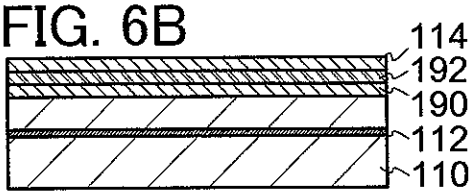


FIG. 6C

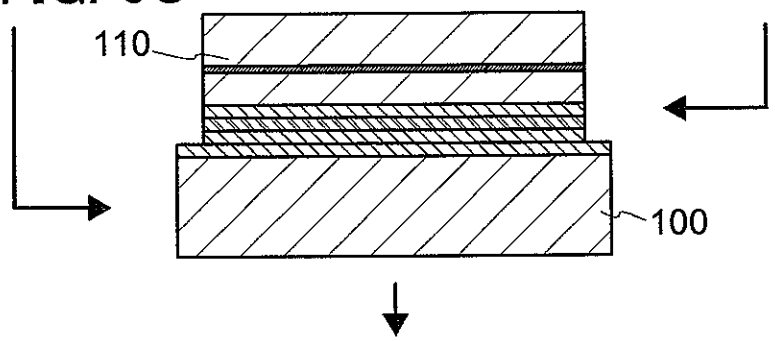


FIG. 6D

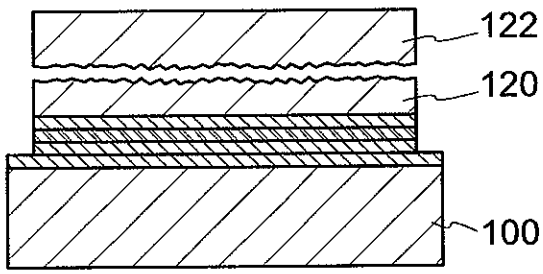


FIG. 6E

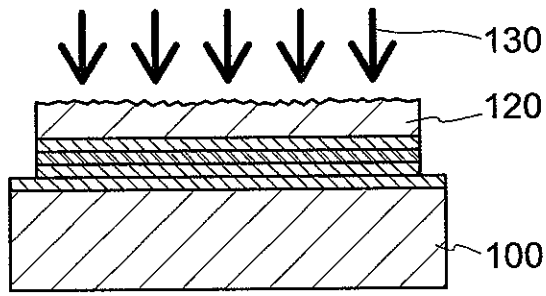


FIG. 6F

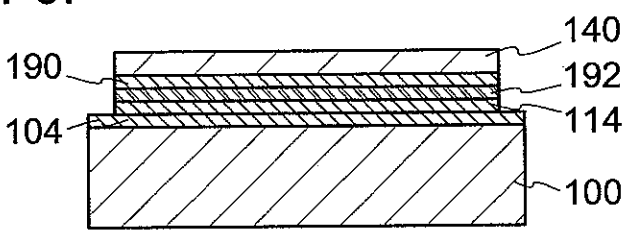


FIG. 7A

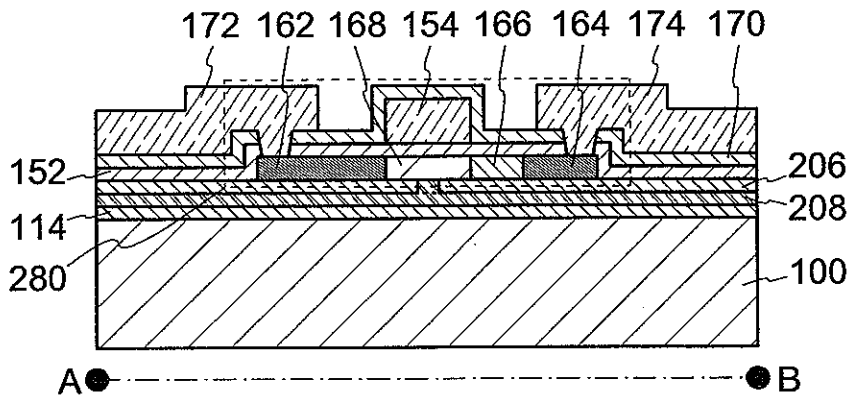

172
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208
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100
A
B

FIG. 7B

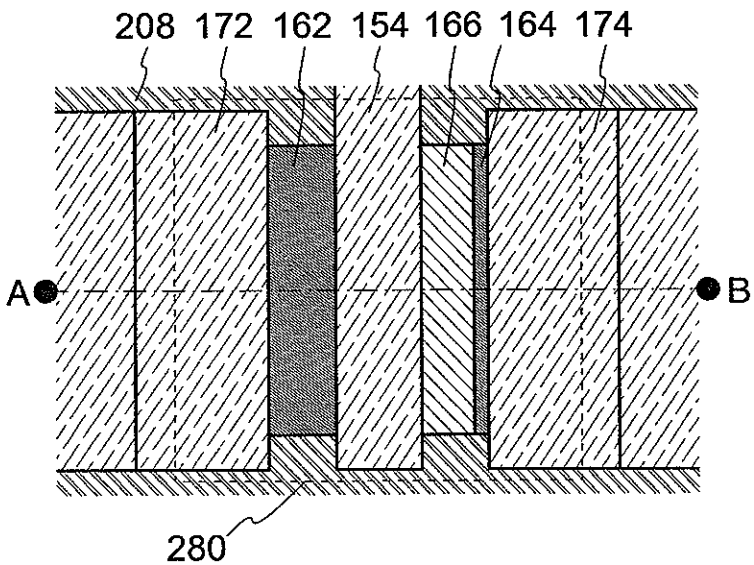

208
172
162
154
166
164
174
A
B
280

FIG. 8A

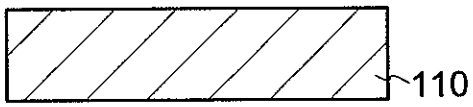


FIG. 8B

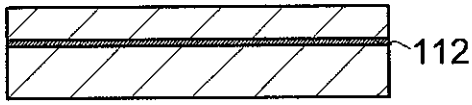


FIG. 8C



FIG. 8D

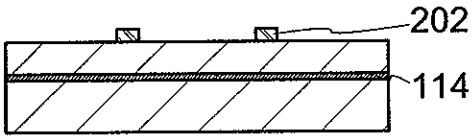


FIG. 8E

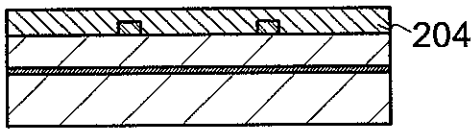


FIG. 8F

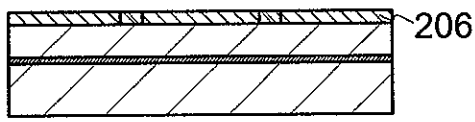


FIG. 8G

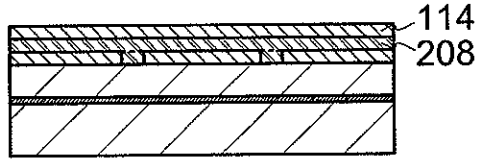


FIG. 9A

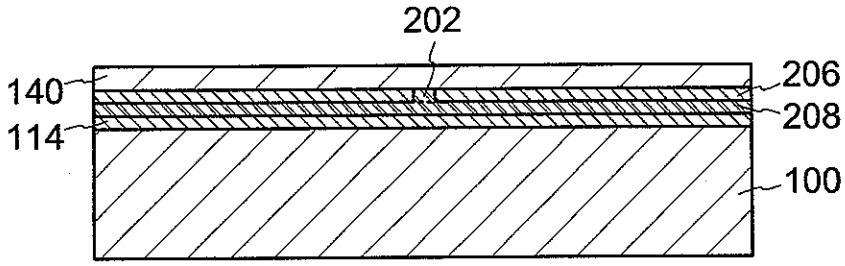


FIG. 9B

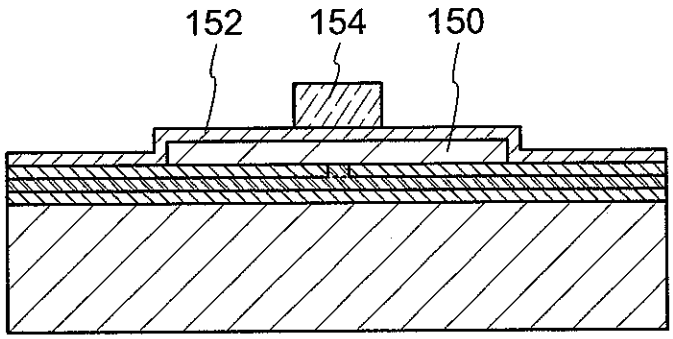


FIG. 9C

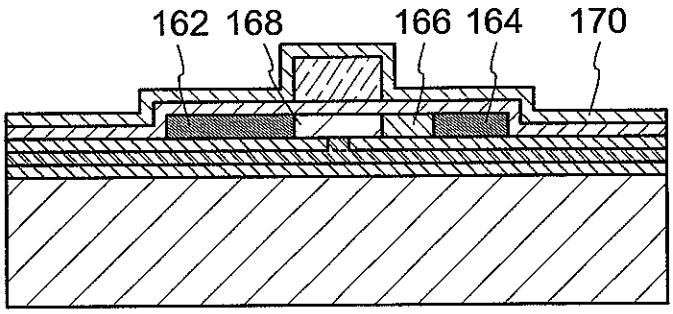


FIG. 9D

